Electronic Supplementary Information

Microwave-assisted hydrothermal synthesis of solid-state carbon dots with intensive emission for white light-emitting devices

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Figure S1 (a) UV-vis absorption spectra, (b) PL emission spectra and (c) blue-to-red spectral composition of Si-CDs at different molar ratios of CA to KH-792.

Figure S2 (a) UV-vis absorption spectra, (b) PL emission spectra and (c) blue-to-red spectral composition at different temperatures.
composition of Si-CDs at different temperatures.

Figure S3 PL emission spectra of C-CDs, K-CDs and Si-CDs prepared at the same conditions.

Figure S4 TGA curve of Si-CDs under N₂ atmosphere.
Figure S5 PL spectra changes of as-prepared Si-CDs under continuous UV ($\lambda_{ex}=365$ nm) radiation.

Inset: Dependence of PL intensity on radiation time for Si-CDs under 365 nm.

Figure S6 AFM image of Si-CDs.